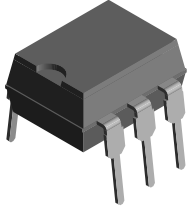
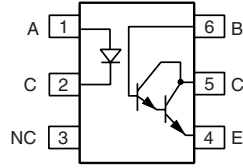




Optocoupler, Photodarlington Output, High Gain, with Base Connection



1179005



FEATURES

- Isolation test voltage: 5300 V_{RMS}
- Coupling capacitance, 0.5 pF
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS COMPLIANT

DESCRIPTION

The H11B1, H11B2, H11B3 are industry standard optocouplers, consisting of a gallium arsenide infrared LED and a silicon photodarlington.

AGENCY APPROVALS

- UL1577, file no. E52744 system code J
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDER INFORMATION	
PART	REMARKS
H11B1	CTR > 500 %, DIP-6
H11B2	CTR > 200 %, DIP-6
H11B3	CTR > 100 %, DIP-6
H11B1-X007	CTR > 500 %, SMD-6 (option 7)
H11B1-X009	CTR > 500 %, SMD-6 (option 9)
H11B2-X009	CTR > 200 %, SMD-6 (option 9)

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	3	V
Forward continuous current		I _F	60	mA
Power dissipation		P _{diss}	100	mW
Derate linearly from 25 °C			1.33	mW/°C
OUTPUT				
Collector emitter breakdown voltage		BV _{CEO}	25	V
Emitter collector breakdown voltage		BV _{ECO}	7	V
Collector base breakdown voltage		BV _{CBO}	30	V
Collector current (continuous)		I _C	100	mA
Power dissipation		P _{diss}	150	mW
Derate linearly from 25 °C			2	mW/°C

H11B1, H11B2, H11B3



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
COUPLER				
Isolation test voltage between emitter and detector		V_{ISO}	5300	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175	
Isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 25 \text{ }^\circ\text{C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{IO} = 500 \text{ V}, T_{amb} = 100 \text{ }^\circ\text{C}$	R_{IO}	$\geq 10^{11}$	Ω
Total package dissipation (LED plus detector)		P_{tot}	260	mW
Derate linearly from 25 °C			3.5	mW/°C
Storage temperature		T_{stg}	- 55 to + 150	°C
Operating temperature		T_{amb}	- 55 to + 100	°C
Lead soldering time at 260 °C			10	s

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 50 \text{ mA}$	H11B1	V_F		1.1	1.5	V
		H11B2	V_F		1.1	1.5	V
	$I_F = 10 \text{ mA}$	H11B3	V_F		1.1	1.5	V
Reverse current	$V_R = 3 \text{ V}$		I_R			10	μA
Junction capacitance	$V_F = 0 \text{ V}, f = 1 \text{ MHz}$		C_j		50		pF
OUTPUT							
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}, I_F = 0 \text{ mA}$		BV_{CEO}	30			V
Emitter collector breakdown voltage	$I_E = 100 \mu\text{A}, I_F = 0 \text{ mA}$		BV_{ECO}	7			V
Collector base breakdown voltage	$I_C = 100 \mu\text{A}, I_F = 0 \text{ mA}$		BV_{CBO}	30			V
Collector emitter leakage current	$V_{CE} = 10 \text{ V}, I_F = 0 \text{ mA}$		I_{CEO}			100	nA
COUPLER							
Saturation voltage collector-emitter	$I_C = 1 \text{ mA}, I_C = 1 \text{ mA}$		V_{CEsat}			1	V
Capacitance (input to output)			C_{IO}		0.5		pF

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC current transfer ratio	$V_{CE} = 5 \text{ V}, I_F = 1 \text{ mA}$	H11B1	CTR_{DC}	500			%
		H11B2	CTR_{DC}	200			%
		H11B3	CTR_{DC}	100			%



SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Switching times	$I_F = 5 \text{ mA}, V_{CE} = 10 \text{ V}, R_L = 100 \Omega$	t_{on}		5		μs
		t_{off}		30		μs

TYPICAL CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

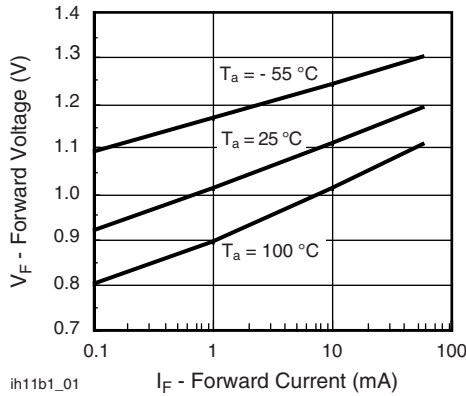


Fig. 1 - Forward Voltage vs. Forward Current

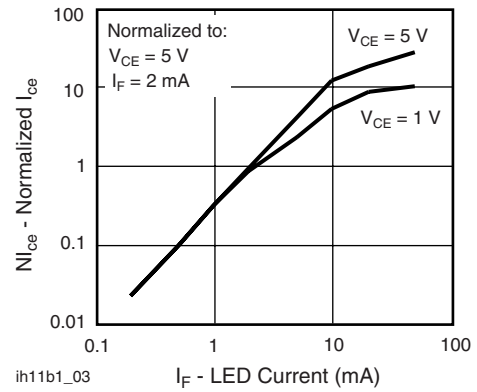


Fig. 3 - Normalized Non-Saturated and Saturated I_{CE} vs. LED Current

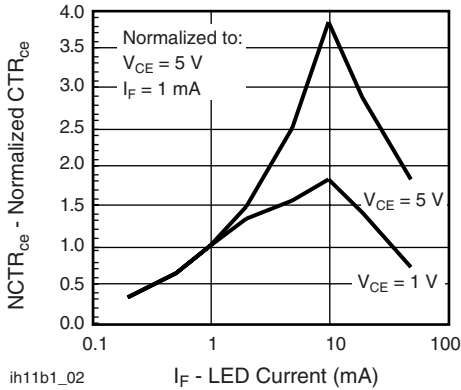


Fig. 2 - Normalized Non-Saturated and Saturated CTR_{CE} vs. LED Current

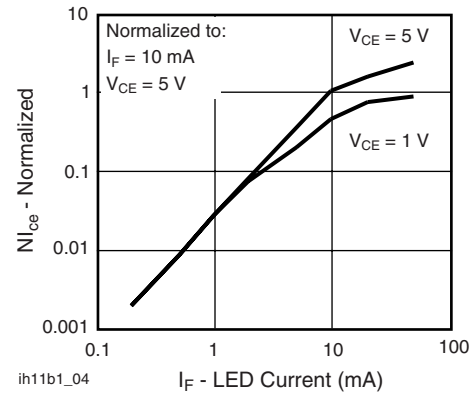


Fig. 4 - Normalized Non-Saturated and Saturated Collector Emitter Current vs. LED Current

H11B1, H11B2, H11B3



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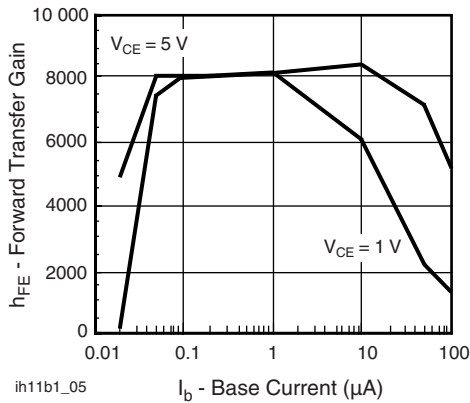


Fig. 5 - Non-Saturated and Saturated h_{FE} vs. Base Current

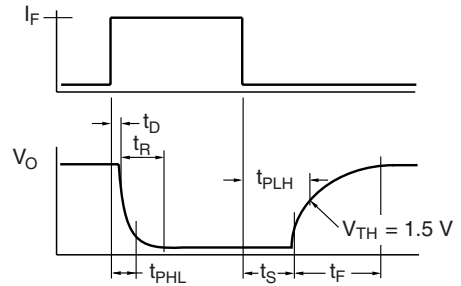


Fig. 8 - Switching Waveform

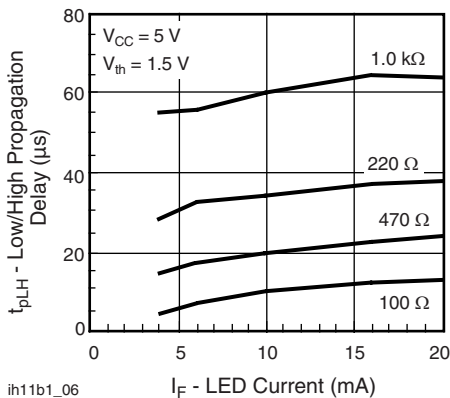


Fig. 6 - Low to High Propagation Delay vs. Collector Load Resistance and LED Current

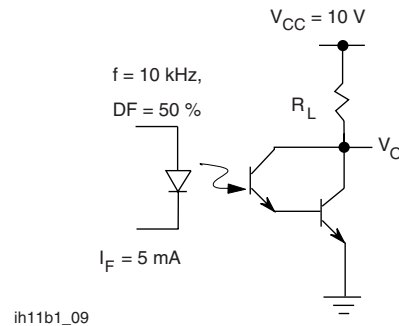


Fig. 9 - Switching Schematic

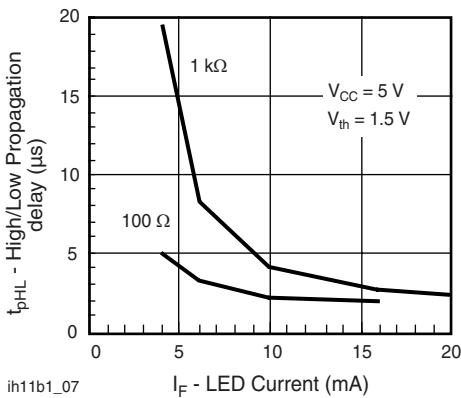


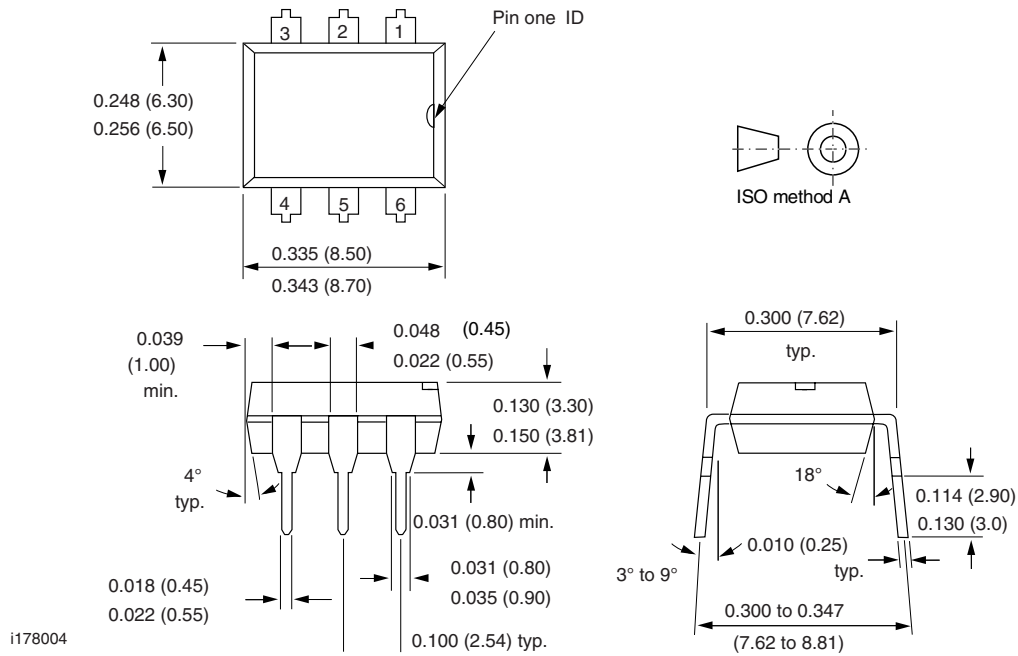
Fig. 7 - High to Low Propagation Delay vs. Collector Load Resistance and LED Current



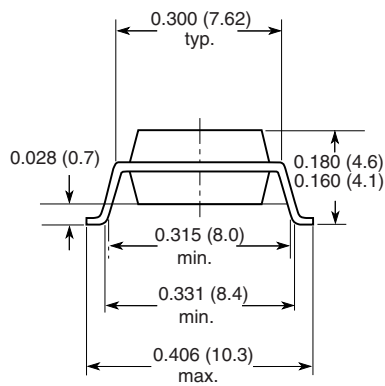
H11B1, H11B2, H11B3

Optocoupler, Photodarlington Output, High Gain, with Base Connection Vishay Semiconductors

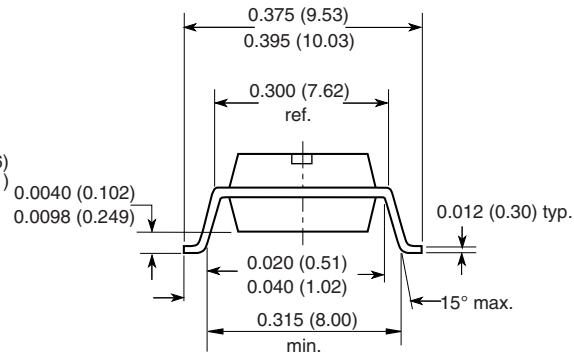
PACKAGE DIMENSIONS in inches (millimeters)



Option 7



Option 9



18494



Vishay Semiconductors Optocoupler, Photodarlington
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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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